



L6201 L6202 - L6203

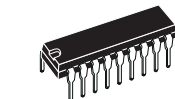
DMOS FULL BRIDGE DRIVER

- SUPPLY VOLTAGE UP TO 48V
- 5A MAX PEAK CURRENT (2A max. for L6201)
- TOTAL RMS CURRENT UP TO
L6201: 1A; L6202: 1.5A; L6203/L6201PS: 4A
- $R_{DS(ON)}$ 0.3 Ω (typical value at 25 °C)
- CROSS CONDUCTION PROTECTION
- TTL COMPATIBLE DRIVE
- OPERATING FREQUENCY UP TO 100 KHz
- THERMAL SHUTDOWN
- INTERNAL LOGIC SUPPLY
- HIGH EFFICIENCY

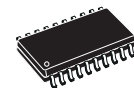
DESCRIPTION

The I.C. is a full bridge driver for motor control applications realized in Multipower-BCD technology which combines isolated DMOS power transistors with CMOS and Bipolar circuits on the same chip. By using mixed technology it has been possible to optimize the logic circuitry and the power stage to achieve the best possible performance. The DMOS output transistors can operate at supply voltages up to 42V and efficiently at high switch-

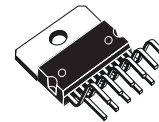
MULTIPOWER BCD TECHNOLOGY



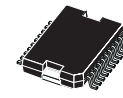
Powerdip 12+3+3



SO20 (12+4+4)



Multiwatt11



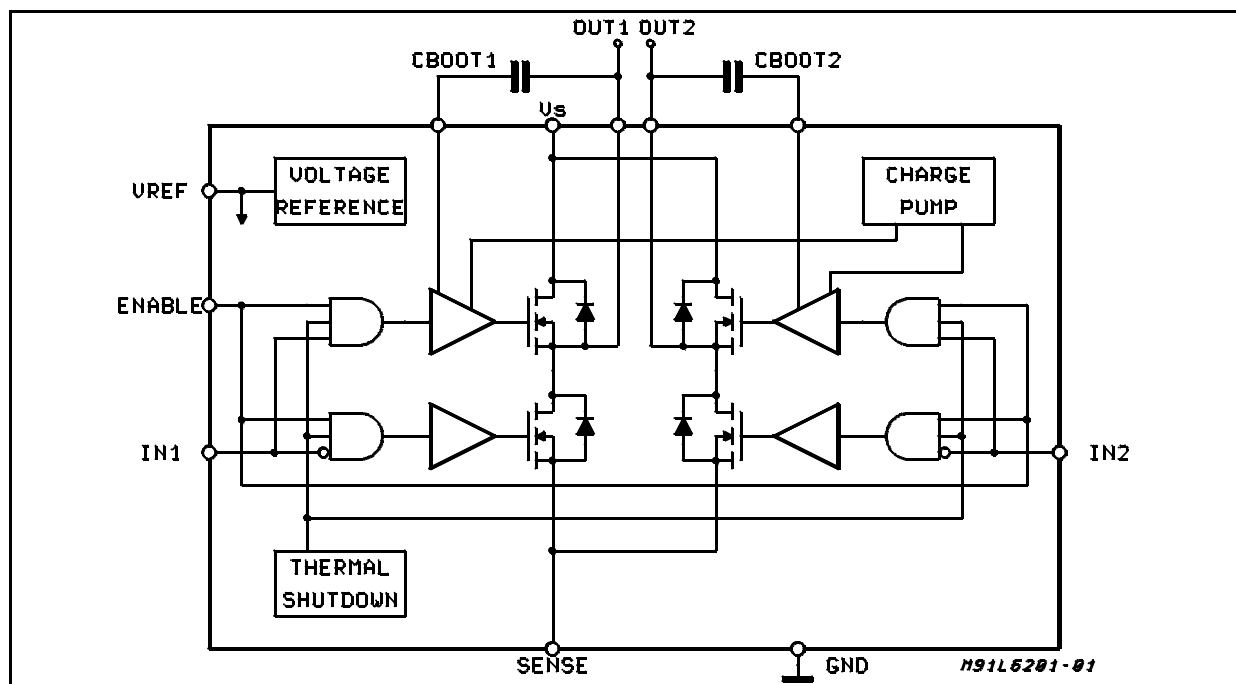
PowerSO20

ORDERING NUMBERS:

L6201 (SO20)
L6201PS (PowerSO20)
L6202 (Powerdip18)
L6203 (Multiwatt)

ing speeds. All the logic inputs are TTL, CMOS and μ C compatible. Each channel (half-bridge) of the device is controlled by a separate logic input, while a common enable controls both channels. The I.C. is mounted in three different packages.

BLOCK DIAGRAM



PINS FUNCTIONS

Device				Name	Function
L6201	L6201PS	L6202	L6203		
1	16	1	10	SENSE	A resistor R_{sense} connected to this pin provides feedback for motor current control.
2	17	2	11	ENAB LE	When a logic high is present on this pin the DMOS POWER transistors are enabled to be selectively driven by IN1 and IN2.
3	2,3,9,12, 18,19	3		N.C.	Not Connected
4,5	–	4	6	GND	Common Ground Terminal
–	1, 10	5		GND	Common Ground Terminal
6,7	–	6		GND	Common Ground Terminal
8	–	7		N.C.	Not Connected
9	4	8	1	OUT2	Output of 2nd Half Bridge
10	5	9	2	V_s	Supply Voltage
11	6	10	3	OUT1	Output of first Half Bridge
12	7	11	4	BOOT1	A bootstrap capacitor connected to this pin ensures efficient driving of the upper POWER DMOS transistor.
13	8	12	5	IN1	Digital Input from the Motor Controller
14,15	–	13	6	GND	Common Ground Terminal
–	11, 20	14		GND	Common Ground Terminal
16,17	–	15		GND	Common Ground Terminal
18	13	16	7	IN2	Digital Input from the Motor Controller
19	14	17	8	BOOT2	A bootstrap capacitor connected to this pin ensures efficient driving of the upper POWER DMOS transistor.
20	15	18	9	V_{ref}	Internal voltage reference. A capacitor from this pin to GND is recommended. The internal Ref. Voltage can source out a current of 2mA max.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_s	Power Supply	52	V
V_{OD}	Differential Output Voltage (between Out1 and Out2)	60	V
V_{IN}, V_{EN}	Input or Enable Voltage	– 0.3 to + 7	V
I_o	Pulsed Output Current for L6201PS/L6202/L6203 (Note 1)	5	A
	– Non Repetitive (< 1 ms) for L6201	5	A
	DC Output Current for L6201PS/L6202/L6203 for L6201 (Note 1)	10 1	A A
V_{sense}	Sensing Voltage	– 1 to + 4	V
V_b	Bootstrap Peak Voltage	60	V
P_{tot}	Total Power Dissipation:		
	$T_{pins} = 90^\circ\text{C}$ for L6201	4	W
	for L6202	5	W
	$T_{case} = 90^\circ\text{C}$ for L6201PS/L6203	20	W
	$T_{amb} = 70^\circ\text{C}$ for L6201 (Note 2)	0.9	W
for L6202 (Note 2)	1.3	W	
for L6201PS/L6203 (Note 2)	2.3	W	
T_{stg}, T_j	Storage and Junction Temperature	– 40 to + 150	$^\circ\text{C}$

Note 1: Pulse width limited only by junction temperature and transient thermal impedance (see thermal characteristics)

Note 2: Mounted on board with minimized dissipating copper area.



L6201 - L6202 - L6203

THERMAL DATA

Symbol	Parameter		Value				Unit
			L6201	L6201PS	L6202	L6203	
R _{th j-pins}	Thermal Resistance Junction-pins	max	15	–	12	–	°C/W
R _{th j-case}	Thermal Resistance Junction Case	max.	–	–	–	3	
R _{th j-amb}	Thermal Resistance Junction-ambient	max.	85	13 (*)	60	35	

(*) Mounted on aluminium substrate.

ELECTRICAL CHARACTERISTICS (Refer to the Test Circuits; T_j = 25°C, V_S = 42V, V_{sens} = 0, unless otherwise specified).

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _s	Supply Voltage		12	36	48	V
V _{ref}	Reference Voltage	I _{REF} = 2mA		13.5		V
I _{REF}	Output Current				2	mA
I _s	Quiescent Supply Current	EN = H V _{IN} = L EN = H V _{IN} = H EN = L (Fig. 1,2,3) I _L = 0		10 10 8	15 15 15	mA mA mA
f _c	Commutation Frequency (*)			30	100	KHz
T _j	Thermal Shutdown			150		°C
T _d	Dead Time Protection			100		ns

TRANSISTORS

OFF						
I _{DSS}	Leakage Current	Fig. 11 V _s = 52 V			1	mA
ON						
R _{DS}	On Resistance	Fig. 4,5		0.3	0.55	Ω
V _{DS(ON)}	Drain Source Voltage	Fig. 9 I _{DS} = 1A I _{DS} = 1.2A I _{DS} = 3A	L6201 L6202 L6201PS/0 3	0.3 0.36 0.9		V V V
V _{sens}	Sensing Voltage			– 1	4	V

SOURCE DRAIN DIODE

V _{sd}	Forward ON Voltage	Fig. 6a and b I _{SD} = 1A L6201 EN = L I _{SD} = 1.2A L6202 EN = L I _{SD} = 3A L6201PS/03 EN = L		0.9 (**) 0.9 (**) 1.35 (**)		V V V
t _{rr}	Reverse Recovery Time	$\frac{dif}{dt} = 25 \text{ A}/\mu\text{s}$ I _F = 1A L6201 I _F = 1.2A L6202 I _F = 3A L6203		300		ns
t _{fr}	Forward Recovery Time			200		ns

LOGIC LEVELS

V _{IN L} , V _{EN L}	Input Low Voltage		– 0.3		0.8	V
V _{IN H} , V _{EN H}	Input High Voltage		2		7	V
I _{IN L} , I _{EN L}	Input Low Current	V _{IN} , V _{EN} = L			–10	μA
I _{IN H} , I _{EN H}	Input High Current	V _{IN} , V _{EN} = H		30		μA

ELECTRICAL CHARACTERISTICS (Continued)
LOGIC CONTROL TO POWER DRIVE TIMING

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t ₁ (V _i)	Source Current Turn-off Delay	Fig. 12		300		ns
t ₂ (V _i)	Source Current Fall Time	Fig. 12		200		ns
t ₃ (V _i)	Source Current Turn-on Delay	Fig. 12		400		ns
t ₄ (V _i)	Source Current Rise Time	Fig. 12		200		ns
t ₅ (V _i)	Sink Current Turn-off Delay	Fig. 13		300		ns
t ₆ (V _i)	Sink Current Fall Time	Fig. 13		200		ns
t ₇ (V _i)	Sink Current Turn-on Delay	Fig. 13		400		ns
t ₈ (V _i)	Sink Current Rise Time	Fig. 13		200		ns

(*) Limited by power dissipation

(**) In synchronous rectification the drain-source voltage drop V_{DS} is shown in fig. 4 (L6202/03); typical value for the L6201 is of 0.3V.

Figure 1: Typical Normalized I_s vs. T_j

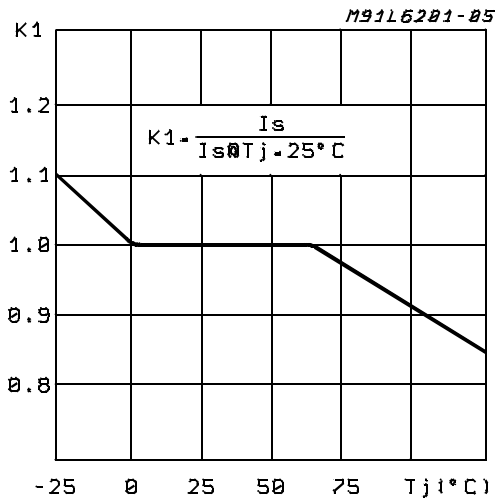


Figure 2: Typical Normalized Quiescent Current vs. Frequency

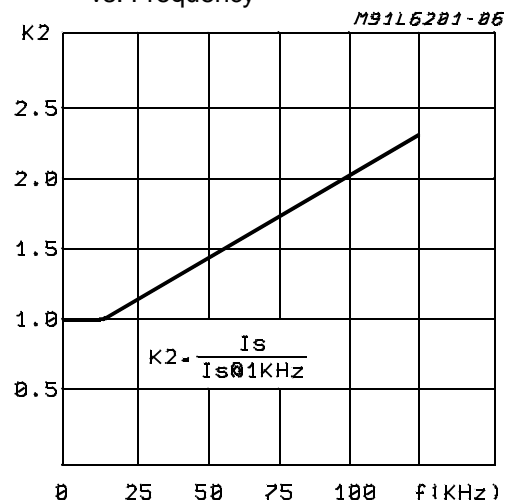


Figure 3: Typical Normalized I_s vs. V_s

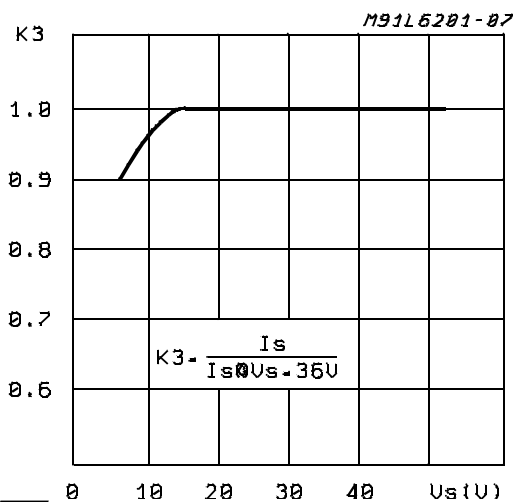


Figure 4: Typical R_{DS(ON)} vs. V_s ~ V_{ref}

